AMENDMENTS TO THE SPECIFICATION

Page 12, please replace paragraph [0057] with the following new paragraph:

[0057] A P-type dopant, such as boron or indium is implanted in substrate layer 215. The implant dose can be between approximately [[5e12]] $5x10^{12}$ atoms/cm^2 to approximately [[1e14]] $1x10^{14}$ atoms/cm^2. In this example the implant dose is approximately [[1e13]] $1x10^{13}$ atoms/cm^2. Multiple implants can be used to tailor the profile of the halo region 236. Also, angled implantation can be conducted to form halo region 236, such that implantation is carried out at angles other than 90 degrees relative to the top surface of substrate layer 215.

Page 14, please replace paragraph [0069] with the following new paragraph:

[0069] Referring to FIG. 8, DRAM cell 200 can include a FinFET 801 having an inert dopant region 839. Inert dopant region 839 is below an edge of gate structure 220 on the side of body 217 opposite to halo region 236 and adjacent to source/drain region 230. Region 839 has an amorphous dopant profile. Illustratively, the peak of the dopant profile lies within buried oxide layer (BOX) 212. Region 839 is formed by implanting inert ions such as argon, germanium, silicon, or other appropriate material. The implant dose used to form region 839 is within the range of approximately [[5e12]] $5x10^{12}$ atoms/cm^2 to approximately 1e16 atoms/cm^2, and is desirably approximately [[1e15]] $1x10^{15}$ atoms/cm^2. Region 839 can be implanted according to the methods described in U.S. Patent No. 6,503,783, by the present inventor, which is incorporated herein by reference in its entirety.